L Number	Hits	Search Text	DB	Time stamp
1	0	("jp-4234173$-$.did.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/21 17:22
2	2	jp-04234173$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/21 17:31
3	2643	((257/135) or (257/328) or (257/339) or (257/354) or (257/355)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/21 17:31
4	213	(((257/135) or (257/328) or (257/339) or (257/354) or (257/355)).CCLS.) and (punch-through or breakdown or punchthrough) and vertical.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/21 17:32
-	3	(vertical adj igfet or v-igfet) and power adj semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/22 17:05
-	34	257/$6.ccls. and power.ti,ab. and igfet.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 21:31
-	1	257/$6.ccls. and power.ti,ab. and (vertical adj igfet or v-igfet).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 21:32
-	20	okabe.in. and igbt.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/28 21:43
-	23	vertical adj igfet.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 10:22
-	0	(portion near3 barrier adj layer) near12 lattice adj match$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 11:42
-	3	("5484740").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 12:3
-	0	("method.clm. and (source adj contact or drain adj contact).clm. and gate.clm. and after.clm. or nefore.clm.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 12:38
-	119	method.clm. and (source adj contact or drain adj contact).clm. and gate.clm. and after.clm. or nefore.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 12:39
-	13	method.clm. and (source adj contact or drain adj contact).clm. same gate.clm. same (after or before).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 13:52

-	3	("5484740").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 15:17
-	2	("6144048").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 15:17
-	3	("5789760").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 15:18
-	0	"64-81270"	JPO	2002/05/29 16:57
-	0	"6481270"	JPO	2002/05/29 16:57
-	0	"36481270"	JPO	2002/05/29 16:57
-	0	"036481270"	JPO	2002/05/29 16:57
-	0	"03-6481270"	JPO	2002/05/29 16:57
-	0	"0364-81270"	JPO	2002/05/29 16:57
-	0	"64-81270"	JPO	2002/05/29 17:00
-	0	jp-6481270$-$.did.	JPO	2002/05/29 17:00
-	0	jp-36481270$-$.did.	JPO	2002/05/29 17:01
-	0	jp-036481270$-$.did.	JPO	2002/05/29 17:01
-	0	jp-81270$-$.did.	JPO	2002/05/29 17:01
-	520	igfet	JPO	2002/05/29 17:01
-	11	igfet and okabe.in.	JPO	2002/05/29 17:05
-	2	igfet and voltage adj diode	JPO	2002/05/29 17:25
-	0	5973338.pn.	JPO	2002/05/29 17:25
-	1	5973338.pn.	USPAT; US-PGPUB	2002/05/29 17:31
-	1	"5399883".PN.	USPAT	2002/05/29 17:26
-	1	"5095343".PN.	USPAT	2002/05/29 17:27
-	1	"4994871".PN.	USPAT	2002/05/29 17:27
-	1	"4994871".PN.	USPAT	2002/05/29 17:27
-	1	"4985743".PN.	USPAT	2002/05/29 17:27
-	81	(257/135).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 17:54
-	3	("5702961").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 19:35
-	81	(257/135).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 19:35
-	0	("L28 and punch-through adj (region or layer)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 19:36
-	0	((257/135).CCLS.) and punch-through adj (region or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 19:36
-	62	punch-through adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 20:08
-	0	ep-0061551$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 20:09

–	0	ep-061551$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 20:13
–	0	ep-0503605$-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 20:13
–	1	"503605"	EPO	2002/05/29 20:16
–	0	(igbt or v-igbt or igfet or v-igfet or vertical adj bipolar adj transistor or vertical adj insulated adj gate).ti,ab. and edge adj termin$5	EPO	2002/05/29 20:18
–	19	(igbt or v-igbt or igfet or v-igfet or vertical adj bipolar adj transistor or vertical adj insulated adj gate).ti,ab. and edge adj termin$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 20:24
–	169	edge adj termination and (257/$6.ccls. or 438/$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 20:25
–	4	edge adj termination and igbt.ti,ab. and (257/$6.ccls. or 438/$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 20:36
–	0	(magneto adj resist$4 or magneto-resist$3) and igbt.ti,ab. and (257/$6.ccls. or 438/$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 20:45
–	11	(channel adj stop$3) and igbt.ti,ab. and (257/$6.ccls. or 438/$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 21:17
–	81	(257/135).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/29 21:17
–	34	(punch adj through or punch-through or punchthrough) and vertical.ti,ab. and (igfet or igbt or v-igbt or v-igfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 10:26
–	1698	((257/339) or (257/354) or (257/355)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 10:53
–	105	(((257/339) or (257/354) or (257/355)).CCLS.) and (vertical or v-igbt ot v-igfet).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 13:57
–	486	(257/328).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 14:18
–	2	("5387528").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 14:23

–	3	("5702961").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 14:23
–	2	("6011280").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 14:24
–	2	("4901127").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 14:25
–	3	("4636830").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 14:25
–	2	("5973338").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 14:26
–	3	("5821586").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 14:26
–	2342	((257/135) or (257/328) or (257/339) or (257/354) or (257/355)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/22 15:48
–	17	(((257/135) or (257/328) or (257/339) or (257/354) or (257/355)).CCLS.) and second adj electrode and vertical.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/22 15:50
–	0	(((257/135) or (257/328) or (257/339) or (257/354) or (257/355)).CCLS.) and compensator and vertical.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/22 15:51
–	0	(((257/135) or (257/328) or (257/339) or (257/354) or (257/355)).CCLS.) and compensator and vertical	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/22 15:51
–	2	("5042043").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 15:13
–	107	(257/79.ccls. or 257/8$5.ccls. or 257/9$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and (buffer adj layer same (amorphous or single adj crystal or crystalline or single-crystal)) and (led or light-emitting or light adj emitting).ti,ab.	USPAT; US-PGPUB	2002/09/23 15:17
–	73	(257/79.ccls. or 257/8$5.ccls. or 257/9$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and (buffer adj layer near10 (amorphous or single adj crystal or crystalline or single-crystal)) and (led or light-emitting or light adj emitting).ti,ab.	USPAT; US-PGPUB	2002/09/23 15:18

		61	(257/79.ccls. or 257/8$5.ccls. or 257/9$5.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and (buffer adj layer near5 (amorphous or single adj crystal or crystalline or single-crystal)) and (led or light-emitting or light adj emitting).ti,ab.	USPAT; US-PGPUB	2002/09/23 15:18
–		16	depletion adj zone near12 (extend or extends or extending or reach or reaches or reaching) and (vertical or vmos or umos or vmosfet or umsofet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 14:17
–		15	(space adj charge or space-charge) adj zone near12 (extend or extends or extending or reach or reaches or reaching) and (vertical or vmos or umos or vmosfet or umsofet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 14:19
–		15	(space adj charge or space-charge) adj zone near12 (extend or extends or extending or reach or reaches or reaching) and (vertical or vmos or umos or vmosfet or umosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 14:42
–		28	(space adj charge or depletion or space-charge) adj zone near12 (extend or extends or extending or reach or reaches or reaching) and (vertical or vmos or umos or vmosfet or umosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 17:57
–		16	(magneto-resistor or magnetoresistor) near6 source and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 17:58
–		2	(magneto-resistor or magnetoresistor) near6 source and power near3 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 18:05
–		2	(magneto-resistor or magnetoresistor) near6 source and power near3 (mos or mosfet or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 18:05
–		16	(magneto-resistor or magnetoresistor) near6 source and (mos or mosfet or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 18:05
–		5	(magneto-resistor or magnetoresistor) near6 source and (mos or mosfet or semiconductor).ti,ab.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 18:14
–		53	deboy.in. and semiconductor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/08 18:15